

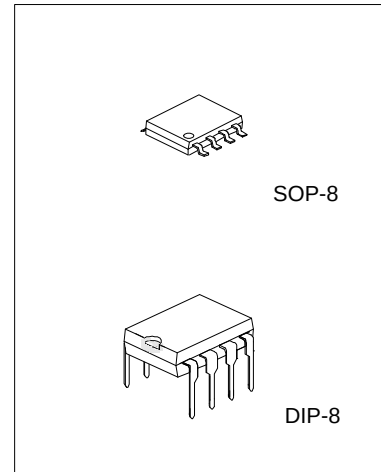
LOW NOISE DUAL J-FET OPERATIONAL AMPLIFIER

DESCRIPTION

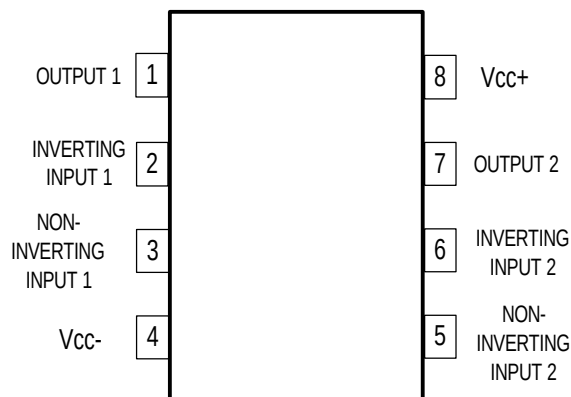
The UTC TL072 is a high speed J-FET input dual operational amplifier. It incorporates well matched, high voltage J-FET and bipolar transistors in a monolithic integrated circuit. The device features high slew rates, low input bias and offset current, and low offset voltage temperature coefficient.

FEATURES

- *Low power consumption
- *Wide common-mode (up to V_{CC}^+) and differential voltage range
- *Low input bias and offset current
- *Low noise $e_n = 15\text{nV} / \sqrt{\text{Hz}}$ (typ)
- *Output short-circuit protection
- *High input impedance J-FET input stage
- *Low harmonic distortion:0.01%(typ)
- *Internal frequency compensation
- *Latch up free operation
- *High slewrate:16V/ μs (typ)

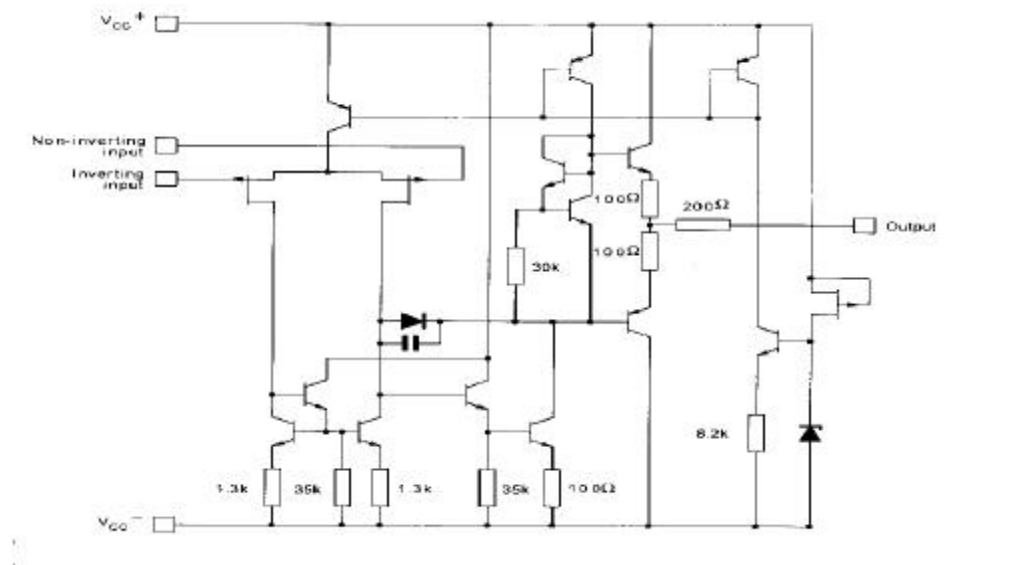


PIN CONFIGURATIONS



UTC TL072 LINEAR INTEGRATED CIRCUIT

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage (note 1)	Vcc	+18	V
Input Voltage (note 2)	Vi	+15	V
Differential Input Voltage (note 3)	Vid	+30	V
Power Dissipation	Ptot	680	mW
Output Short-Circuit Duration (Note 4)		Infinite	
Operating Free Air Temperature Range	Toper	0 to 70	°C
Storage Temperature Range	Tstg	-65 to 150	°C

- NOTES: 1. All voltage values, except differential voltage, are with respect to the zero reference level (ground) of the supply voltages where the zero reference level is the midpoint between Vcc- and Vcc+.
2. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 volts, whichever is less.
3. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal.
4. The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

UTC TL072 LINEAR INTEGRATED CIRCUIT

UTC TL072C ELECTRICAL CHARACTERISTICS($V_{CC}=+/-15V$, $T_a=25^{\circ}C$, unless otherwise specified)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Input Offset Voltage($R_s=50\Omega$, $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$)	V_{io}		3	10 13	mV
Temperature Coefficient of Input Offset Voltage($R_s=50\Omega$)	D_{vio}		10		$\mu V/^{\circ}C$
Input Offset Current* $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	I_{io}		5	100 10	pA nA
Input Bias Current* $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	I_{ib}		20	200 20	pA nA
Input Common Mode Voltage	V_{icm}	+11	-12~+15		V
Output Voltage Swing($R_L=10k\Omega$) $T_a=25^{\circ}C$, $R_L=2k\Omega$, $T_a=25^{\circ}C$, $R_L=10k\Omega$ $T_{min} \leq T_a \leq T_{max}$, $R_L=2k\Omega$ $T_{min} \leq T_a \leq T_{max}$, $R_L=10k\Omega$	V_{opp}	10 12 10 12	12 13.5		V
Large Signal Voltage Gain($R_L=10k\Omega$, $V_o=+/-10V$) $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	A_{vd}	25 15	200		V/mV
Gain Bandwidth Product($T_a=25^{\circ}C$, $R_L=10k\Omega$, $C_L=100pF$)	GBP	2.5	4		MHz
Input Resistance	R_i		10^{12}		Ω
Common Mode Rejection Ratio($R_s=50\Omega$) $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	CMR	70 70	86		dB
Supply Voltage Rejection Ratio($R_s=50\Omega$) $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	SVR	70 70	86		dB
Supply Current(no load) $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	I_{cc}		1.4	2.5 2.5	mA
Channel Separation($A_v=100$, $T_a=25^{\circ}C$)	V_{01}/V_{02}		120		dB
Output Short-circuit Current $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	I_{os}	10 10	40	60 60	mA
Slew Rate($V_i=10V$, $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, unity gain)	SR	8	16		V/ μs
Rise Time($V_i=20mV$, $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, unity gain)	t_r		0.1		μs
Overshoot Factor($V_i=20mV$, $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, unity gain)	K_{ov}		10		%
Total Harmonic Distortion($A_v=20dB$, $f=1kHz$ $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, $V_o=2V_{pp}$)	THD		0.01		%
Phase Margin			45		Degrees
Equivalent Input Noise Voltage($R_s=100\Omega$, $f=1KHz$)	e_n		15		

*The Input bias currents are junction leakage currents, which approximately double for every $10^{\circ}C$ increase in the junction temperature.

UTC TL072AC ELECTRICAL CHARACTERISTICS($V_{CC}=+-15V$, $T_a=25^{\circ}C$, unless otherwise specified)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Input Offset Voltage($R_s=50\Omega$, $T_a=25^{\circ}C$ $T_{min}\leq T_a\leq T_{max}$)	V_{io}		3	6 7	mV
Temperature Coefficient of Input Offset Voltage($R_s=50\Omega$)	D_{vio}		10		$\mu V/^{\circ}C$
Input Offset Current* $T_a=25^{\circ}C$ $T_{min}\leq T_a\leq T_{max}$	I_{io}		5	100 4	pA nA
Input Bias Current* $T_a=25^{\circ}C$ $T_{min}\leq T_a\leq T_{max}$	I_{ib}		20	200 20	pA nA
Input Common Mode Voltage	V_{icm}	+11	-12~+15		V
Output Voltage Swing($R_L=10k\Omega$) $T_a=25^{\circ}C$, $R_L=2k\Omega$, $T_a=25^{\circ}C$, $R_L=10k\Omega$ $T_{min}\leq T_a\leq T_{max}$, $R_L=2k\Omega$ $T_{min}\leq T_a\leq T_{max}$, $R_L=10k\Omega$	V_{opp}	10 12 10 12	12 13.5		V
Large Signal Voltage Gain($R_L=10k\Omega$, $V_o=+-10V$) $T_a=25^{\circ}C$ $T_{min}\leq T_a\leq T_{max}$	A_{vd}	50 25	200		V/mV
Gain Bandwidth Product($T_a=25^{\circ}C$, $R_L=10k\Omega$, $C_L=100pF$)	GBP	2.5	4		MHz
Input Resistance	R_i		10^{12}		Ω
Common Mode Rejection Ratio($R_s=50\Omega$) $T_a=25^{\circ}C$ $T_{min}\leq T_a\leq T_{max}$	CMR	80 80	86		dB
Supply Voltage Rejection Ratio($R_s=50\Omega$) $T_a=25^{\circ}C$ $T_{min}\leq T_a\leq T_{max}$	SVR	80 80	86		dB
Supply Current(no load) $T_a=25^{\circ}C$ $T_{min}\leq T_a\leq T_{max}$	I_{cc}		1.4	2.5 2.5	mA
Channel Separation($A_v=100$, $T_a=25^{\circ}C$)	V_{o1}/V_{o2}		120		dB
Output Short-circuit Current $T_a=25^{\circ}C$ $T_{min}\leq T_a\leq T_{max}$	I_{os}	10 10	40	60 60	mA
Slew Rate($V_i=10V$, $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, unity gain)	SR	8	16		V/ μs
Rise Time($V_i=20mV$, $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, unity gain)	t_r		0.1		μs
Overshoot Factor($V_i=20mV$, $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, unity gain)	K_{ov}		10		%
Total Harmonic Distortion($A_v=20dB$, $f=1kHz$ $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, $V_o=2V_{pp}$)	THD		0.01		%
Phase Margin			45		Degrees
Equivalent Input Noise Voltage($R_s=100\Omega$, $f=1kHz$)	e_n		15		

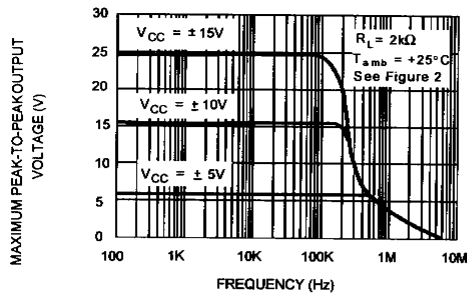
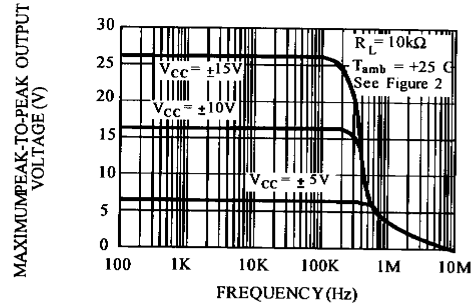
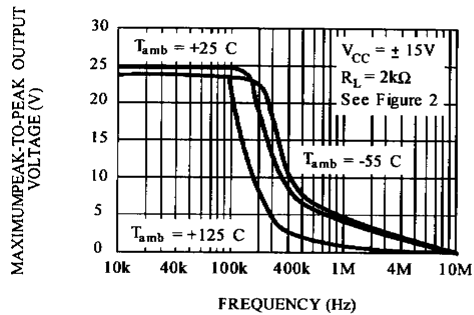
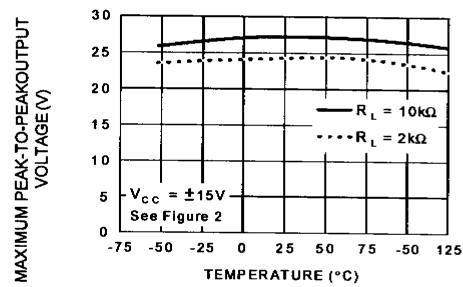
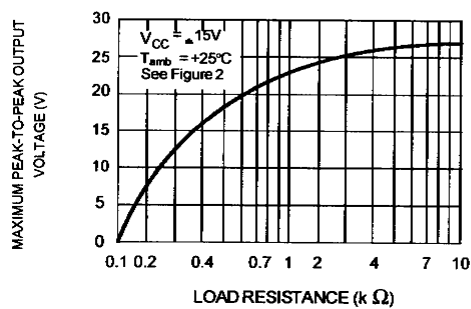
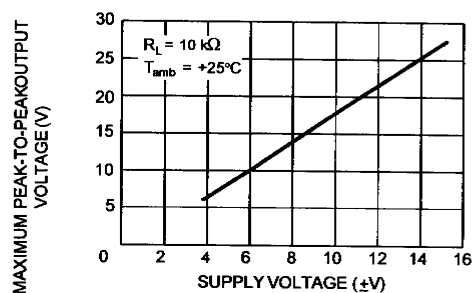
*The Input bias currents are junction leakage currents, which approximately double for every $10^{\circ}C$ increase in the junction temperature.

UTC TL072 LINEAR INTEGRATED CIRCUIT

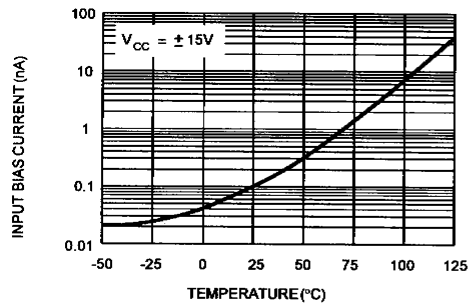
UTC TL072BC ELECTRICAL CHARACTERISTICS($V_{CC}=+-15V$, $T_a=25^{\circ}C$, unless otherwise specified)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Input Offset Voltage($R_s=50\Omega$), $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	V_{io}		1	3 5	mV
Temperature Coefficient of Input Offset Voltage($R_s=50\Omega$)	D_{vio}		10		$\mu V/^{\circ}C$
Input Offset Current* $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	I_{io}		5	100 4	pA nA
Input Bias Current* $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	I_{ib}		20	200 20	pA nA
Input Common Mode Voltage	V_{icm}	+11	-12~+15		V
Output Voltage Swing($R_L=10k\Omega$) $T_a=25^{\circ}C$, $R_L=2k\Omega$ $T_a=25^{\circ}C$, $R_L=10k\Omega$ $T_{min} \leq T_a \leq T_{max}$, $R_L=2k\Omega$ $T_{min} \leq T_a \leq T_{max}$, $R_L=10k\Omega$	V_{opp}	10 12 10 12	12 13.5		V
Large Signal Voltage Gain($R_L=10k\Omega$, $V_o=+-10V$) $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	A_{vd}	50 25	200		V/mV
Gain Bandwidth Product($T_a=25^{\circ}C$, $R_L=10k\Omega$, $C_L=100pF$)	GBP	2.5	4		MHz
Input Resistance	R_i		10^{12}		Ω
Common Mode Rejection Ratio($R_s=50\Omega$) $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	CMR	80 80	86		dB
Supply Voltage Rejection Ratio($R_s=50\Omega$) $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	SVR	80 80	86		dB
Supply Current(no load) $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	I_{cc}		1.4	2.5 2.5	mA
Channel Separation($A_v=100$, $T_a=25^{\circ}C$)	V_{o1}/V_{o2}		120		dB
Output Short-circuit Current $T_a=25^{\circ}C$ $T_{min} \leq T_a \leq T_{max}$	I_{os}	10 10	40	60 60	mA
Slew Rate($V_i=10V$, $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, unity gain)	SR	8	16		V/ μs
Rise Time($V_i=20mV$, $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, unity gain)	t_r		0.1		μs
Overshoot Factor($V_i=20mV$, $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, unity gain)	K_{ov}		10		%
Total Harmonic Distortion($A_v=20dB$, $f=1kHz$, $R_L=2k\Omega$, $C_L=100pF$, $T_a=25^{\circ}C$, $V_o=2V_{pp}$)	THD		0.01		%
Phase Margin			45		Degrees
Equivalent Input Noise Voltage($R_s=100\Omega$, $f=1kHz$)	e_n		15		

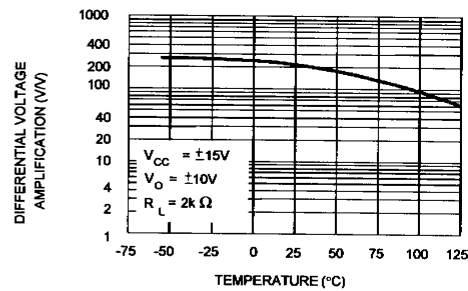
*The Input bias currents are junction leakage currents, which approximately double for every $10^{\circ}C$ increase in the junction temperature.

**MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS FREQUENCY**

**MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS FREQUENCY**

**MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS FREQUENCY**

**MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS FREE AIR TEMP.**

**MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS LOAD RESISTANCE**

**MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS SUPPLY VOLTAGE**


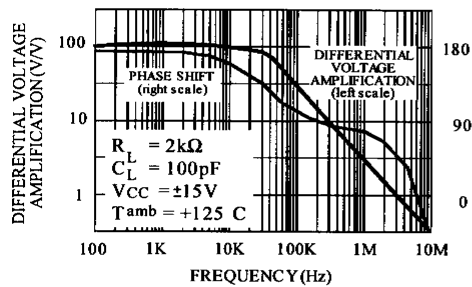
**INPUT BIAS CURRENT VERSUS
FREE AIR TEMPERATURE**



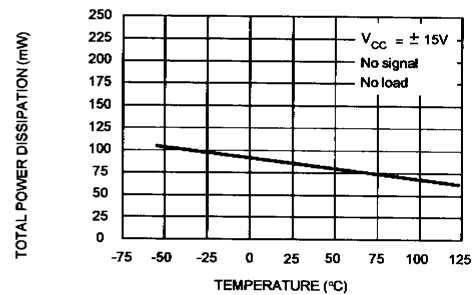
**LARGE SIGNAL DIFFERENTIAL
VOLTAGE AMPLIFICATION VERSUS
FREE AIR TEMPERATURE**



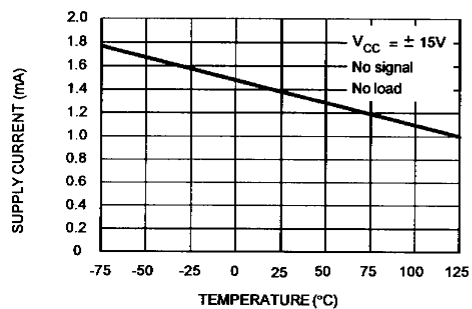
**LARGE SIGNAL DIFFERENTIAL
VOLTAGE AMPLIFICATION AND PHASE
SHIFT VERSUS FREQUENCY**



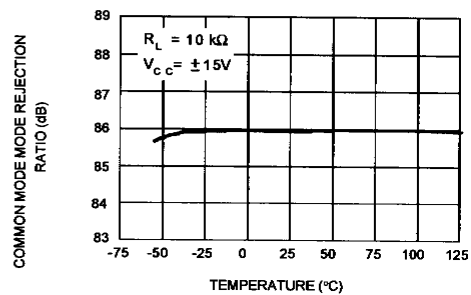
**TOTAL POWER DISSIPATION VERSUS
FREE AIR TEMPERATURE**

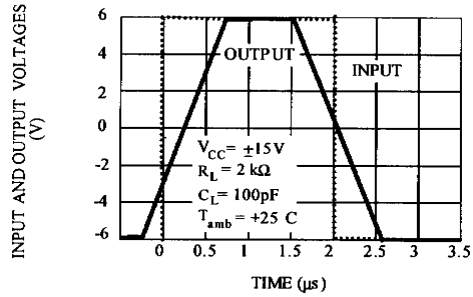
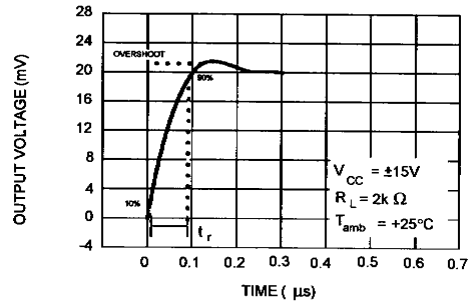
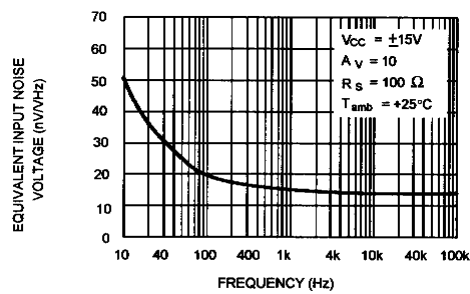
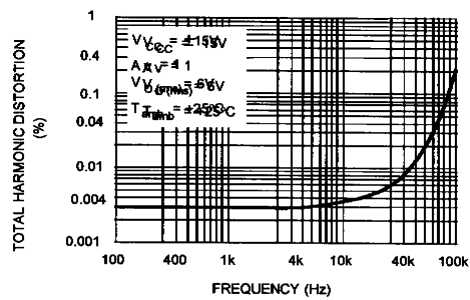


**SUPPLY CURRENT PER AMPLIFIER
VERSUS FREE AIR TEMPERATURE**



**COMMON MODE REJECTION RATIO
VERSUS FREE AIR TEMPERATURE**



VOLTAGE FOLLOWER LARGE SIGNAL
PULSE RESPONSEOUTPUT VOLTAGE VERSUS
ELAPSED TIMEEQUIVALENT INPUT NOISE VOLTAGE
VERSUS FREQUENCYTOTAL HARMONIC DISTORTION VERSUS
FREQUENCY

UTC TL072 LINEAR INTEGRATED CIRCUIT

PARAMETER MEASUREMENT INFORMATION

Figure 1 : Voltage Follower

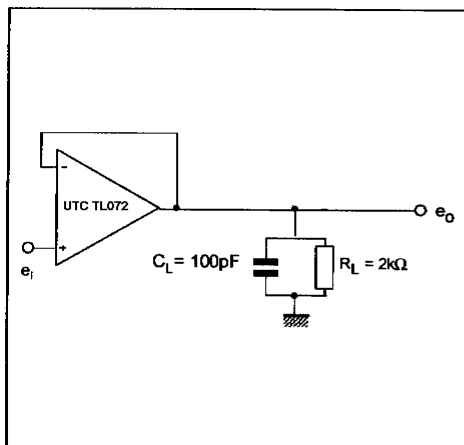


Figure 2 : Gain-of-10 Inverting Amplifier

